

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Claims:

Claims 1, 9, 10, and 19 have been amended as follows:

1. (Twice Amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WN film, a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.

9. (Twice Amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body,

the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WN film, a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.

10. (Twice Amended) An ohmic electrode obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WN film, a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.

19. (Twice Amended) An ohmic electrode provided on a III-V compound semiconductor body obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprised of In and a film including at least a metal nitride film,

the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WN film, a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.

CONCLUSION

In view of the foregoing, it is submitted that claims 1-19 are patentable. It is therefore submitted that the application is in condition for allowance. Notice to that effect is respectfully requested.

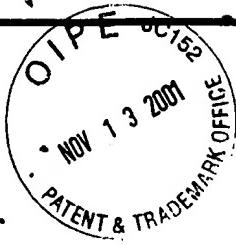
Respectfully submitted,

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Continued Prosecution Application Request under 37 CFR 1.53(d) of prior U.S. application
Serial No. 08/809,463

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